

This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

Claims 1-4 canceled.

Cancel claim 5.

Claim 6 (previously presented). A method of depositing a ferroelectric thin film comprising:

preparing a substrate;

forming a high-k layer overlying the substrate by depositing a high-k material selected from the group consisting of hafnium oxide, zirconium oxide, aluminum oxide, and lanthanum oxide;

depositing an indium oxide film on the substrate; and

depositing a ferroelectric material on the indium oxide thin film using MOCVD.

Cancel claim 7.

Claim 8 (original). The method of claim 6, further comprising annealing the indium oxide film at a temperature between about 400 °C and about 800 °C for between about 5 minutes and about 60 minutes in an oxygen atmosphere.

Cancel claim 9-12.

Claims 13-19 canceled.